

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	487	(bombard\$4) same spacers	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:03
L3	10409	(implant\$4 or dop\$4) same spacers same sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:51
L4	3853	3 and CMOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 15:42
L5	5533	(implant\$4 or dop\$4) with spacers with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:17
L6	2251	5 and CMOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:17
L7	4172	(dop\$4) with spacers with sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:17
L8	606	7 and (argon or ar or xenon or inert)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:47
L9	116	wieczorek-karsten.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:48
L10	2248	(imping\$4 or anneal\$4) same spacers same sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 13:52

L11	29	(imping\$4 or anneal\$4) same spacers same sidewall same (argon or xenon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 14:12
L12	462	(imping\$4 or anneal\$4) with spacers with ions	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 14:39
L13	822	(imping\$4 or anneal\$4) same (SIN or "silicon nitride") same sidewall	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 14:12
L14	574	(imping\$4 or anneal\$4) same (SIN or "silicon nitride") same sidewall same etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 15:08
L15	445	anneal\$4 with spacers with ions	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 14:57
L16	5	anneal\$4 with spacers with (argon or Ar or xenon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 14:58
L17	105	anneal\$4 same spacers same (argon or Ar or xenon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 14:58
L18	58	(anneal\$4) same (SIN or "silicon nitride") same "etch rate"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 15:41
L19	2640	(anneal\$4) same (SIN or "silicon nitride") same etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 15:48
L20	759	19 and CMOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 15:42

L21	125	(anneal\$4) same (ar or argon or inert) same (SIN or "silicon nitride") same etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/19 15:49
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